L660-35M32L Higher beam type LED

L660-35M32L is an AlGaAs LED mounted on TO-18 stem and hermetically sealed with glass ball lens can being designed for high beam uses.
On forward bias it emits a spectral band of radiation, which peaks at 660nm.

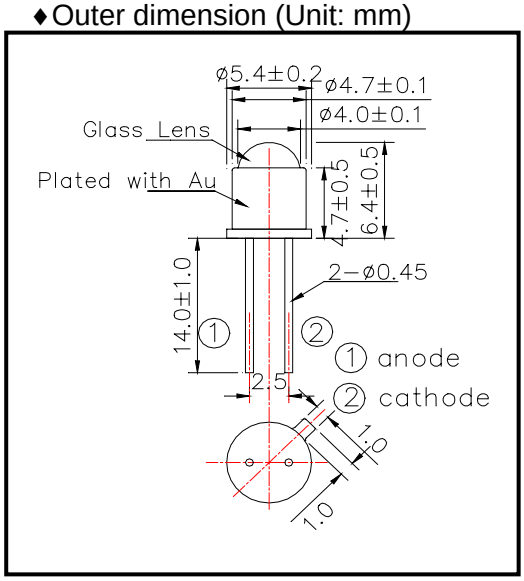
♦Features

1) High Power
2) High Reliability
3) Narrow viewing angle

♦Specifications

1) Product Name	LED Lamp
2) Type No.	L660-35M32L
3) Chip Spec.	
(1) Material	AlGaAs
(2) Chip dimension	350um*350um
(2) Peak Wavelength	660nm
4) Package	
(1) Type	TO-18 Stem
(2) Lens	Glass Ball Lens
(3) Cap	Gold plated

♦Outer dimension (Unit: mm)



♦Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P_D	120	mW	Ta=25°C
Forward Current	I_F	50	mA	Ta=25°C
Pulse Forward Current	I_{FP}	75	mA	Ta=25°C
Reverse Voltage	V_R	5	V	Ta=25°C
Operating Temperature	T_{OPR}	-30 ~ +85	°C	
Storage Temperature	T_{STG}	-30 ~ +100	°C	
Soldering Temperature	T_{SOL}	260	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.
‡Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

♦Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V_F	I_F=20mA		1.9	2.2	V
Reverse Current	I_R	V_R=5V			10	uA
Total Radiated Power	P_O	I_F=20mA		1.7		mW
Radiant Intensity	I_E	I_F=20mA		18		mWsr
Brightness	I_V	I_F=20mA		1800		mcd
Peak Wavelength	λ_P	I_F=20mA	645	655	665	nm
Half Width	$\Delta\lambda$	I_F=20mA		20		nm
Viewing Half Angle	$\theta_{1/2}$	I_F=20mA		±6		deg.

‡Total Radiated Power is measured by Photodyne #500
‡Radiant Intensity is measured by Tektronix J-6512.

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